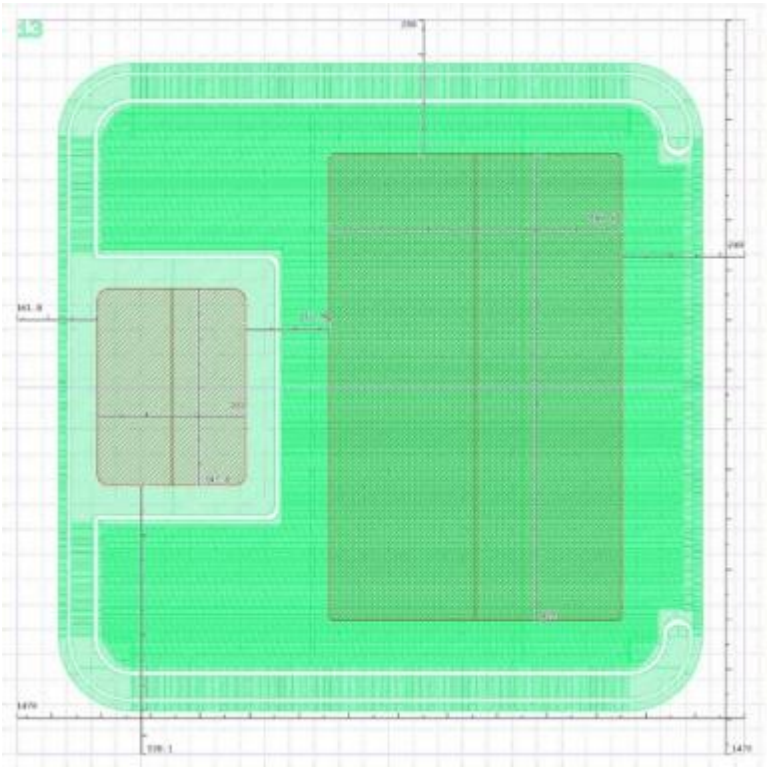
Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Easy to Parallel
- Simple to Drive
- RoHS Compliant

Part NO.		MSM180065B
V_{dss}	=	650 V
$R_{dson(@10A)}$	=	180moh
$I_{D@\ (25℃)}$	=	20 A

Wafer Parameters

Parameter	Typ.	Unit
Die Size(with SL)	1530x 1530	μm
Scribe Line	80	μm
Anode Pad Opening	1250 x1250	μm
Wafer Diameter	150	mm
Thickness	150±10	μm
Anode Metalization (Al)	4	μm
Cathode Metalization (Ti/Ni/Ag)	0.1/0.5/1	μm
Grossdie	7780	pcs



Maximum ratings

Symbol	Parameter	Test conditions	Value	Unit
VDS	Drain-Source Voltage		650	V
ID	Continuous Drain Current	Tc=25°C Tc=100°	20 16.5	A
IDM	Peak Drain Current	Pulse width tp limited by Tjmax	100	A
VGSmax	Gate-Source Voltage		-8/+22	V
VGSop	Recommend Gate-Source Voltage		0/15	V
Tj	Operating Junction Temperature		-55~175	℃

Electrical Characteristics

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-Source Breakdown Voltage	ID=100μA, VGS=0V		650		V
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=10mA Tj=25°C Tj=175°C		3.5 2.8		V
RDS(on)	Drain-Source On-State Resistance	VGS=15V,ID=10A Tj=25°C Tj=175°C		160 195		mΩ